

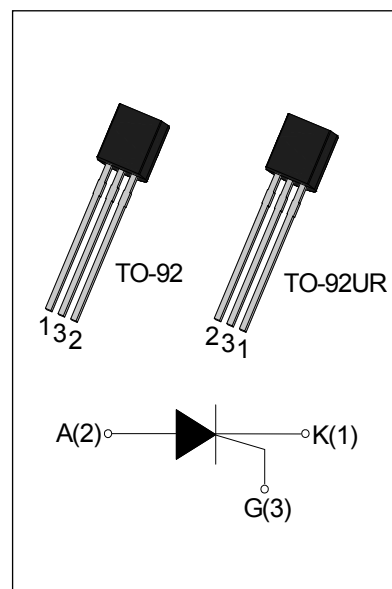


DESCRIPTION:

The JX008 series SCR provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package TO-92 & TO-92UR are RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
I_{GT}	≤ 200	μA
V_{DRM}/V_{RRM}	600	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range		T_j	-40-125 ^①	$^{\circ}C$
Repetitive peak off-state voltage		V_{DRM}	600	V
Repetitive peak reverse voltage		V_{RRM}	600	V
RMS on-state current	TO-92/TO-92UR ($T_C=65^{\circ}C$)	$I_{T(RMS)}$	0.8	A
Non repetitive surge peak on-state current (F=50Hz tp=10ms)		I_{TSM}	8	A
Non repetitive surge peak on-state current (F=60Hz tp=8.3ms)		I_{TSM}	9	A
I^2t value for fusing (tp=10ms)		I^2t	0.32	A^2s
Critical rate of rise of on-state current		di/dt	50	A/ μs
Peak gate current (tp=20 μs , $T_j=125^{\circ}C$)		I_{GM}	0.2	A
Peak gate power (tp=20 μs , $T_j=125^{\circ}C$)		P_{GM}	0.5	W
Average gate power dissipation($T_j=125^{\circ}C$)		$P_{G(AV)}$	0.1	W

NOTE 1: When we parallel connect a $\leq 1K\Omega$ resistor between Gate and Cathode, the T_j can reach $125^{\circ}C$; if without this resistor, the T_j only can reach $110^{\circ}C$.

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	20	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	4	mA
I_H	$I_T=0.05\text{A}$	-	-	3	mA
dV/dt	$V_D=400\text{V}$ $T_j=125^{\circ}\text{C}$ $R_{GK}=1\text{K}\Omega$	600	-	-	V/ μs
dV/dt	$V_D=400\text{V}$ $T_j=125^{\circ}\text{C}$ $R_{GK}=220\Omega$	1000	-	-	V/ μs
t_{on}	$I_G=10\text{mA}$ $I_A=4\text{mA}$ $I_R=0.4\text{mA}$ $T_j=25^{\circ}\text{C}$	-	2	-	μs
t_{off}		-	50	-	μs
R_d	Dynamic Resistance $T_j=125^{\circ}\text{C}$	-	-	35	m Ω

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_T=1.1\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	100	μA

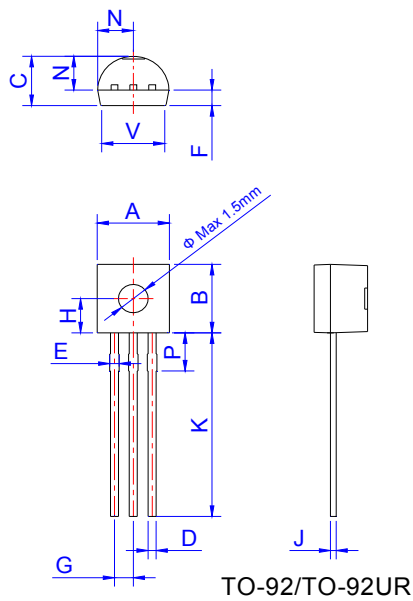
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-92/TO-92UR	75	$^{\circ}\text{C/W}$

ORDERING INFORMATION

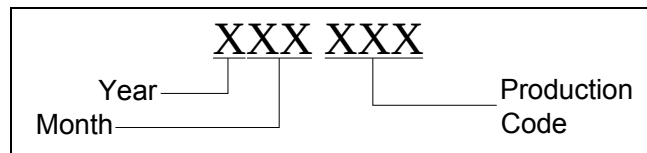
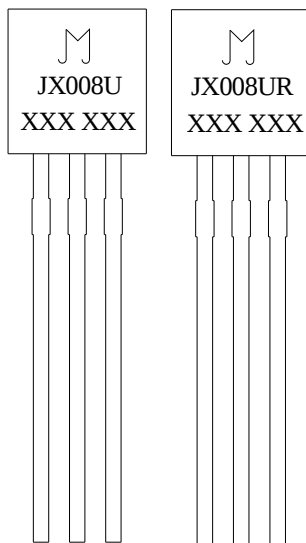
J		X	008	U
JieJie Microelectronics Co.,Ltd				U:TO-92 UR:TO-92UR
Sensitive gate SCRs			$I_{T(RMS)}:0.8\text{A}$	

PACKAGE MECHANICAL DATA

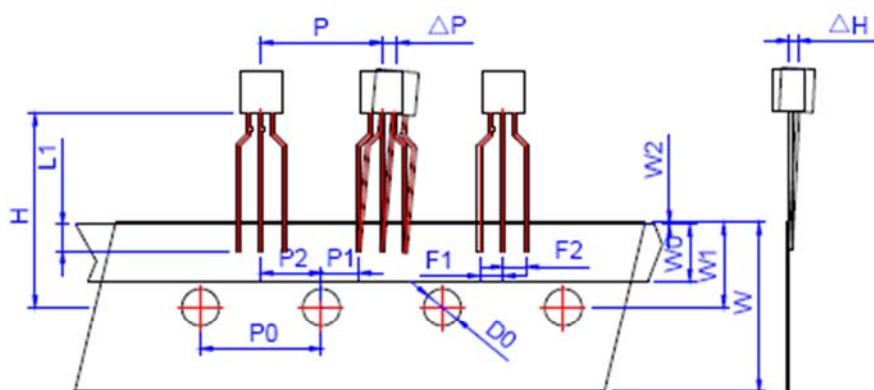


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

MARKING

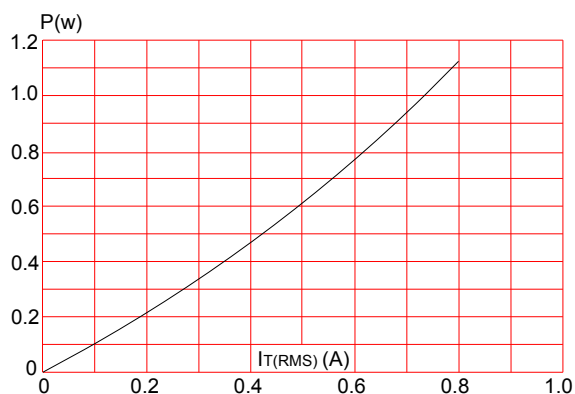
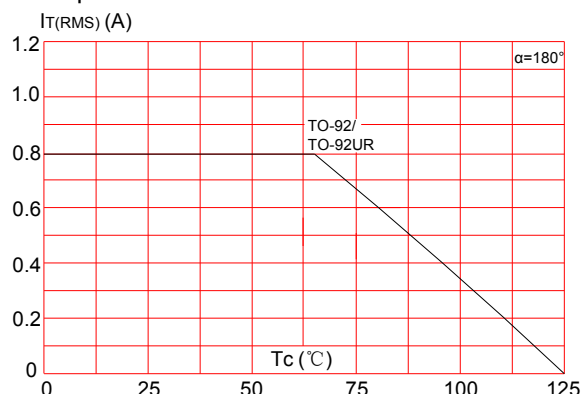
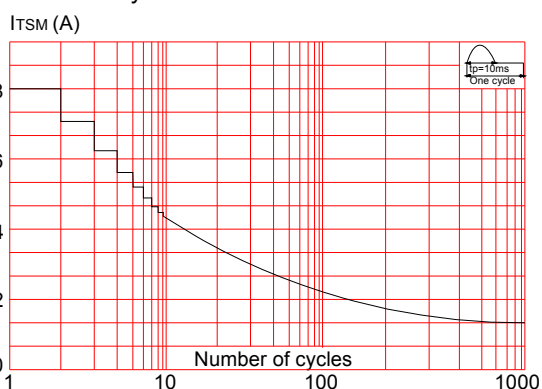
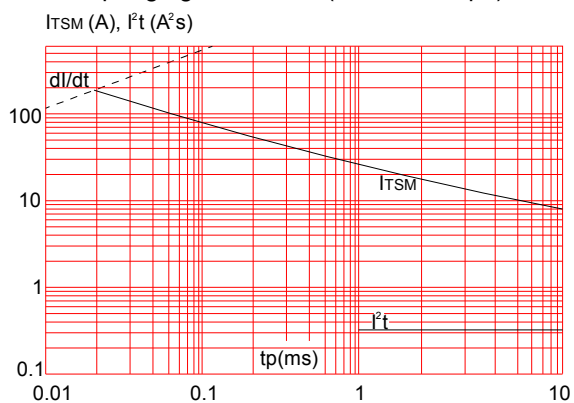
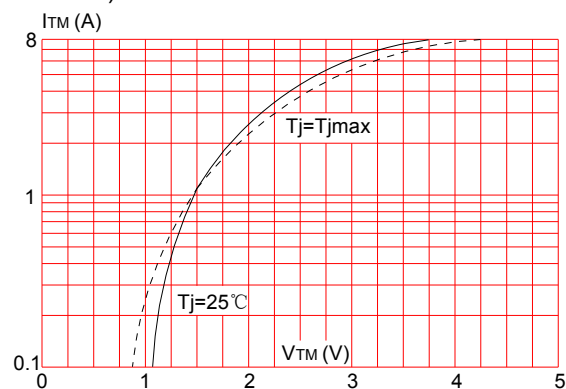
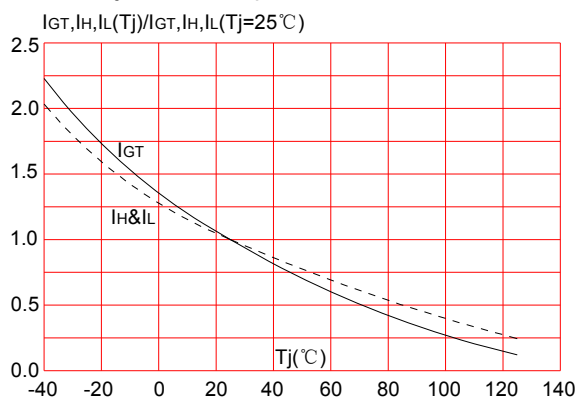


PACKAGE INFORMATION



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
P	12.40	12.70	13.00	0.488	0.500	0.512
P0	12.40	12.70	13.00	0.488	0.500	0.512
P1	3.55	3.85	4.15	0.140	0.152	0.163
P2	6.05	6.35	6.65	0.238	0.250	0.262
ΔP	-1.0	0	1.0	-0.039	0	0.039
F1, F2	2.20	2.50	2.80	0.087	0.098	0.110
F1-F2	-0.3	0	0.3	-0.012	0	0.012
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.50	6.00	6.50	0.217	0.236	0.256
W1	8.50	9.00	9.50	0.335	0.354	0.374
W2			1.0			0.039
D0	3.80	4.0	4.20	0.150	0.157	0.165
ΔH	-1.0	0	1.0	-0.039	0	0.039
L1	2.5			0.098		
H	18.0	19.0	20.0	0.709	0.748	0.787

Packaging Information	Reel	Inner Box	Outer Box
Net Weight (g)	140	80	600
Quantity (pcs)	/	2000	20000
N. W. Per Unit (mg/pcs)	189		

FIG.1 Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

FIG.4: On-state characteristics (maximum values)

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


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